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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	625
Number of Logic Elements/Cells	5000
Total RAM Bits	169984
Number of I/O	86
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-5e-6mn132i

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Secondary Clock/Control Sources

LatticeXP2 devices derive secondary clocks (SC0 through SC7) from eight dedicated clock input pads and the rest from routing. Figure 2-7 shows the secondary clock sources.

Figure 2-7. Secondary Clock Sources





LatticeXP2-30 and smaller devices have six secondary clock regions. All devices in the LatticeXP2 family have four secondary clocks (SC0 to SC3) which are distributed to every region.

The secondary clock muxes are located in the center of the device. Figure 2-12 shows the mux structure of the secondary clock routing. Secondary clocks SC0 to SC3 are used for clock and control and SC4 to SC7 are used for high fan-out signals.







Figure 2-14. Slice0 through Slice2 Control Selection



Edge Clock Routing

LatticeXP2 devices have eight high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. Each device has two edge clocks per edge. Figure 2-15 shows the selection muxes for these clocks.

Figure 2-15. Edge Clock Mux Connections





sysMEM Memory

LatticeXP2 devices contains a number of sysMEM Embedded Block RAM (EBR). The EBR consists of 18 Kbit RAM with dedicated input and output registers.

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-5. FIFOs can be implemented in sysMEM EBR blocks by using support logic with PFUs. The EBR block supports an optional parity bit for each data byte to facilitate parity checking. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

FlashBAK EBR Content Storage

All the EBR memory in the LatticeXP2 is shadowed by Flash memory. Optionally, initialization values for the memory blocks can be defined using the Lattice Diamond design tools. The initialization values are loaded into the Flash memory during device programming and into the SRAM at power up or whenever the device is reconfigured. This feature is ideal for the storage of a variety of information such as look-up tables and microprocessor code. It is also possible to write the current contents of the EBR memory back to Flash memory. This capability is useful for the storage of data such as error codes and calibration information. For additional information on the FlashBAK capability see TN1137, LatticeXP2 Memory Usage Guide.



For further information on the sysMEM EBR block, please see TN1137, LatticeXP2 Memory Usage Guide.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the low-to-high transition of the reset signal, as shown in Figure 2-18. The GSR input to the EBR is always asynchronous.



Reset	
Clock	
Clock —————— Enable	

If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of 1/f_{MAX} (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device Wake Up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM and ROM implementations.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

sysDSP™ Block

The LatticeXP2 family provides a sysDSP block making it ideally suited for low cost, high performance Digital Signal Processing (DSP) applications. Typical functions used in these applications include Bit Correlators, Fast Fourier Transform (FFT) functions, Finite Impulse Response (FIR) Filter, Reed-Solomon Encoder/Decoder, Turbo Encoder/ Decoder and Convolutional Encoder/Decoder. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

sysDSP Block Approach Compare to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. The LatticeXP2 family, on the other hand, has many DSP blocks that support different data-widths. This allows the designer to use highly parallel implementations of DSP functions. The designer can optimize the DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-19 compares the fully serial and the mixed parallel and serial implementations.



register. Similarly, CE and RST are selected from their four respective sources (CE0, CE1, CE2, CE3 and RST0, RST1, RST2, RST3) at each input register, pipeline register and output register.

Signed and Unsigned with Different Widths

The DSP block supports other widths, in addition to x9, x18 and x36 widths, of signed and unsigned multipliers. For unsigned operands, unused upper data bits should be filled to create a valid x9, x18 or x36 operand. For signed two's complement operands, sign extension of the most significant bit should be performed until x9, x18 or x36 width is reached. Table 2-7 provides an example of this.

Table 2-7. Sign Extension Example

Number	Unsigned	Unsigned 9-bit	Unsigned 18-bit	Signed	Two's Complement Signed 9 Bits	Two's Complement Signed 18 Bits
+5	0101	000000101	00000000000000101	0101	00000101	00000000000000101
-6	N/A	N/A	N/A	1010	111111010	1111111111111111010

OVERFLOW Flag from MAC

The sysDSP block provides an overflow output to indicate that the accumulator has overflowed. "Roll-over" occurs and an overflow signal is indicated when any of the following is true: two unsigned numbers are added and the result is a smaller number than the accumulator, two positive numbers are added with a negative sum or two negative numbers are added with a positive sum. Note that when overflow occurs the overflow flag is present for only one cycle. By counting these overflow pulses in FPGA logic, larger accumulators can be constructed. The conditions for the overflow signal for signed and unsigned operands are listed in Figure 2-24.

Figure 2-24. Accumulator Overflow/Underflow





IPexpress[™]

The user can access the sysDSP block via the Lattice IPexpress tool, which provides the option to configure each DSP module (or group of modules), or by direct HDL instantiation. In addition, Lattice has partnered with The Math-Works[®] to support instantiation in the Simulink[®] tool, a graphical simulation environment. Simulink works with Diamond to dramatically shorten the DSP design cycle in Lattice FPGAs.

Optimized DSP Functions

Lattice provides a library of optimized DSP IP functions. Some of the IP cores planned for the LatticeXP2 DSP include the Bit Correlator, FFT functions, FIR Filter, Reed-Solomon Encoder/Decoder, Turbo Encoder/Decoder and Convolutional Encoder/Decoder. Please contact Lattice to obtain the latest list of available DSP IP cores.

Resources Available in the LatticeXP2 Family

Table 2-8 shows the maximum number of multipliers for each member of the LatticeXP2 family. Table 2-9 shows the maximum available EBR RAM Blocks and Serial TAG Memory bits in each LatticeXP2 device. EBR blocks, together with Distributed RAM can be used to store variables locally for fast DSP operations.

Device	DSP Block	9x9 Multiplier	18x18 Multiplier	36x36 Multiplier
XP2-5	3	24	12	3
XP2-8	4	32	16	4
XP2-17	5	40	20	5
XP2-30	7	56	28	7
XP2-40	8	64	32	8

Table 2-8. Maximum Number of DSP Blocks in the LatticeXP2 Family

Table 2-9. Embedded SRAM/TAG Memor	v in the LatticeXP2 Family

Device	EBR SRAM Block	Total EBR SRAM (Kbits)	TAG Memory (Bits)
XP2-5	9	166	632
XP2-8	12	221	768
XP2-17	15	276	2184
XP2-30	21	387	2640
XP2-40	48	885	3384

LatticeXP2 DSP Performance

Table 2-10 lists the maximum performance in Millions of MAC (MMAC) operations per second for each member of the LatticeXP2 family.

Table 2-10. DSP Performance

Device	DSP Block	DSP Performance MMAC
XP2-5	3	3,900
XP2-8	4	5,200
XP2-17	5	6,500
XP2-30	7	9,100
XP2-40	8	10,400

For further information on the sysDSP block, please see TN1140, <u>LatticeXP2 sysDSP Usage Guide</u>.



shows the diagram using this gearbox function. For more information on this topic, see TN1138, <u>LatticeXP2 High</u> <u>Speed I/O Interface</u>.







Figure 2-28. DQS Input Routing (Left and Right)

	PIO A		PADA "T"
	PIO B		PADB "C"
	PIO A		PADA "T"
	PIO B	· · · · ·	PADB "C"
	PIO A		PADA "T"
	PIO B	↓+	PADB "C"
	PIO A		PADA "T"
	PIO B	┃┣	PADB "C"
DOG	PIO A	sysIO Buffer	
 ■ DQ5 		Delay	LVDS Pair
+ DQS	PIO B	Delay	LVDS Pair
↓ DQS	PIO B PIO A		PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
	→ PIO B → PIO A → PIO B		PADA "1" LVDS Pair PADB "C" PADA "T" LVDS Pair LVDS Pair PADA "C"
	→ PIO B → PIO A → PIO B → PIO A		PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
			PADA T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair LVDS Pair PADB "C"
			PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C"

Figure 2-29. DQS Input Routing (Top and Bottom)

	PIO A		PADA "T"
	PIO B	+	PADB "C"
	PIO A		PADA "T"
	PIO B	· · · · ·	PADB "C"
—	PIO A		PADA "T" LVDS Pair
	PIO B	→	PADB "C"
—	PIO A		PADA "T"
<u> </u>	PIO B	→	PADB "C"
	PIO A	syslO Buffer	·
DQS		Palay	
•		Delay	LVDS Pair
	PIO B		LVDS Pair I I PADB "C" I
	PIO B PIO A		LVDS Pair I PADB "C"
	→ PIO B → PIO A → PIO B		LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C"
	→ PIO B → PIO A → PIO B → PIO A		LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair
	→ PIO B → PIO A → PIO B → PIO A → PIO B		LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADA "C" PADA "C"
	→ PIO B → PIO A → PIO A → PIO A → PIO A → PIO B → PIO A		LVDS Pair PADA "T" LVDS Pair PADA "T" PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADA "T" LVDS Pair
			LVDS Pair PADA "T" LVDS Pair PADA "T" PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADB "C"
			LVDS Pair PADA "T" LVDS Pair PADB "C" PADB "C" PADB "C" PADB "C" PADB "C" PADB "C" PADB "C" PADA "T" LVDS Pair PADB "C" PADA "T" LVDS Pair PADA "T" LVDS Pair



Hot Socketing Specifications^{1, 2, 3, 4}

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I _{DK}	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX.)	_	_	+/-1	mA

1. Insensitive to sequence of V_{CC} , V_{CCAUX} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} , V_{CCAUX} and V_{CCIO} .

2. $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX) or $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).

3. I_{DK} is additive to I_{PU} , I_{PW} or I_{BH} .

4. LVCMOS and LVTTL only.

ESD Performance

Please refer to the <u>LatticeXP2 Product Family Qualification Summary</u> for complete qualification data, including ESD performance.

DC Electrical Characteristics

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I _{IL} , I _{IH} 1	Input or I/O Low Leakage	$0 \le V_{IN} \le V_{CCIO}$	—		10	μΑ
		$V_{CCIO} \le V_{IN} \le V_{IH}$ (MAX)	—	—	150	μΑ
I _{PU}	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7 \ V_{CCIO}$	-30	—	-150	μΑ
I _{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\leq V_{IN} \leq V_{CCIO}$	30		210	μΑ
I _{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	μΑ
I _{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μΑ
I _{BHLO}	Bus Hold Low Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—		210	μΑ
I _{BHHO}	Bus Hold High Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	-150	μΑ
V _{BHT}	Bus Hold Trip Points		V_{IL} (MAX)	_	V _{IH} (MIN)	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 \text{ to } V_{IH} \text{ (MAX)}$	—	8	—	pf
C2	Dedicated Input Capacitance	$V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 \text{ to } V_{IH} \text{ (MAX)}$	—	6	—	pf

Over Recommended Operating Conditions

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. T_A 25°C, f = 1.0 MHz.



Programming and Erase Flash Supply Current^{1, 2, 3, 4, 5}

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical (25°C, Max. Supply) ⁶	Units
		XP2-5	17	mA
	Core Power Supply Current	XP2-8	21	mA
I _{CC}		XP2-17	28	mA
		XP2-30	36	mA
		XP2-40	50	mA
I _{CCAUX}		XP2-5	64	mA
	Auxiliary Power Supply Current ⁷	XP2-8	66	mA
		XP2-17	83	mA
		XP2-30	87	mA
		XP2-40	88	mA
I _{CCPLL}	PLL Power Supply Current (per PLL)		0.1	mA
I _{CCIO}	Bank Power Supply Current (per Bank)		5	mA
I _{CCJ}	V _{CCJ} Power Supply Current ⁸		14	mA

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.

3. Frequency 0 MHz (excludes dynamic power from FPGA operation).

4. A specific configuration pattern is used that scales with the size of the device; consists of 75% PFU utilization, 50% EBR, and 25% I/O configuration.

5. Bypass or decoupling capacitor across the supply.

6. $T_J = 25^{\circ}C$, power supplies at nominal voltage.

 In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual auxiliary supply current is the sum of I_{CCAUX} and I_{CCPLL}. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the auxiliary power supply.

8. When programming via JTAG.



Table 3-1. LVDS25E DC Conditions

Parameter	Description	Typical	Units
V _{CCIO}	Output Driver Supply (+/-5%)	2.50	V
Z _{OUT}	Driver Impedance	20	Ω
R _S	Driver Series Resistor (+/-1%)	158	Ω
R _P	Driver Parallel Resistor (+/-1%)	140	Ω
R _T	Receiver Termination (+/-1%)	100	Ω
V _{OH}	Output High Voltage (after R _P)	1.43	V
V _{OL}	Output Low Voltage (after R _P)	1.07	V
V _{OD}	Output Differential Voltage (After R _P)	0.35	V
V _{CM}	Output Common Mode Voltage	1.25	V
Z _{BACK}	Back Impedance	100.5	Ω
I _{DC}	DC Output Current	6.03	mA

LVCMOS33D

All I/O banks support emulated differential I/O using the LVCMOS33D I/O type. This option, along with the external resistor network, provides the system designer the flexibility to place differential outputs on an I/O bank with 3.3V VCCIO. The default drive current for LVCMOS33D output is 12mA with the option to change the device strength to 4mA, 8mA, 16mA or 20mA. Follow the LVCMOS33 specifications for the DC characteristics of the LVCMOS33D.



LVPECL

The LatticeXP2 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL



Table 3-3. LVPECL DC Conditions¹

Parameter	Description	Typical	Units
V _{CCIO}	Output Driver Supply (+/-5%)	3.30	V
Z _{OUT}	Driver Impedance	10	Ω
R _S	Driver Series Resistor (+/-1%)	93	Ω
R _P	Driver Parallel Resistor (+/-1%)	196	Ω
R _T	Receiver Termination (+/-1%)	100	Ω
V _{OH}	Output High Voltage (After R _P)	2.05	V
V _{OL}	Output Low Voltage (After R _P)	1.25	V
V _{OD}	Output Differential Voltage (After R _P)	0.80	V
V _{CM}	Output Common Mode Voltage	1.65	V
Z _{BACK}	Back Impedance	100.5	Ω
I _{DC}	DC Output Current	12.11	mA

Over Recommended Operating Conditions

1. For input buffer, see LVDS table.



LatticeXP2 Internal Switching Characteristics¹ (Continued)

		-7		-6		-5		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{RST_PIO}	Asynchronous reset time for PFU Logic	—	0.386	—	0.419	—	0.452	ns
t _{DEL}	Dynamic Delay Step Size	0.035	0.035	0.035	0.035	0.035	0.035	ns
EBR Timing	· · · · · ·							
t _{CO_EBR}	Clock (Read) to Output from Address or Data	_	2.774	_	3.142	_	3.510	ns
t _{COO_EBR}	Clock (Write) to Output from EBR Output Register	_	0.360	—	0.408	—	0.456	ns
t _{SUDATA_EBR}	Setup Data to EBR Memory (Write Clk)	-0.167	_	-0.198	_	-0.229	_	ns
t _{HDATA_EBR}	Hold Data to EBR Memory (Write Clk)	0.194	—	0.231	_	0.267	—	ns
t _{SUADDR_EBR}	Setup Address to EBR Memory (Write Clk)	-0.117	—	-0.137	_	-0.157	—	ns
t _{HADDR_EBR}	Hold Address to EBR Memory (Write Clk)	0.157	—	0.182	_	0.207	—	ns
t _{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory (Write/Read Clk)	-0.135	—	-0.159	_	-0.182	—	ns
t _{HWREN_EBR}	Hold Write/Read Enable to EBR Memory (Write/Read Clk)	0.158	—	0.186	_	0.214	_	ns
t _{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register (Read Clk)	0.144	—	0.160	_	0.176	_	ns
t _{HCE_EBR}	Clock Enable Hold Time to EBR Output Register (Read Clk)	-0.097	—	-0.113	_	-0.129	_	ns
t _{RSTO_EBR}	Reset To Output Delay Time from EBR Output Register (Asynchro- nous)	_	1.156	_	1.341	_	1.526	ns
t _{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	-0.117	—	-0.137	_	-0.157	_	ns
t _{HBE_EBR}	Byte Enable Hold Time to EBR Output Register Dynamic Delay on Each PIO	0.157	_	0.182	_	0.207	_	ns
t _{RSTREC_EBR}	Asynchronous reset recovery time for EBR	0.233	—	0.291		0.347	—	ns
t _{RST_EBR}	Asynchronous reset time for EBR	—	1.156	—	1.341	_	1.526	ns
PLL Paramete	ers							
t _{RSTKREC_PLL}	After RSTK De-assert, Recovery Time Before Next Clock Edge Can Toggle K-divider Counter	1.000	_	1.000		1.000	_	ns
t _{RSTREC_PLL}	After RST De-assert, Recovery Time Before Next Clock Edge Can Toggle M-divider Counter (Applies to M-Divider Portion of RST Only ²)	1.000	_	1.000	_	1.000	_	ns
DSP Block Tir	DSP Block Timing							
t _{SUI_DSP}	Input Register Setup Time	0.135	—	0.151	—	0.166	—	ns
t _{HI_DSP}	Input Register Hold Time	0.021	—	-0.006	—	-0.031	—	ns
t _{SUP_DSP}	Pipeline Register Setup Time	2.505	—	2.784	—	3.064	—	ns

Over Recommended Operating Conditions



EBR Timing Diagrams





Note: Input data and address are registered at the positive edge of the clock and output data appears after the positive edge of the clock.

Figure 3-7. Read/Write Mode with Input and Output Registers





On-Chip Oscillator and Configuration Master Clock Characteristics

Parameter	Min.	Max.	Units	
Master Clock Frequency	Selected value -30%	Selected value +30%	MHz	
Duty Cycle	40	60	%	

Over Recommended Operating Conditions

Figure 3-9. Master SPI Configuration Waveforms











LatticeXP2 Family Data Sheet Ordering Information

February 2012

Data Sheet DS1009

Part Number Description



Ordering Information

The LatticeXP2 devices are marked with a single temperature grade, either Commercial or Industrial, as shown below.



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Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5F484I	1.2V	-5	fpBGA	484	IND	40
LFXP2-40E-6F484I	1.2V	-6	fpBGA	484	IND	40
LFXP2-40E-5F672I	1.2V	-5	fpBGA	672	IND	40
LFXP2-40E-6F672I	1.2V	-6	fpBGA	672	IND	40



LatticeXP2 Family Data Sheet Supplemental Information

February 2012

Data Sheet DS1009

For Further Information

A variety of technical notes for the LatticeXP2 FPGA family are available on the Lattice Semiconductor web site at <u>www.latticesemi.com</u>.

- TN1136, LatticeXP2 sysIO Usage Guide
- TN1137, LatticeXP2 Memory Usage Guide
- TN1138, LatticeXP2 High Speed I/O Interface
- TN1126, LatticeXP2 sysCLOCK PLL Design and Usage Guide
- TN1139, Power Estimation and Management for LatticeXP2 Devices
- TN1140, LatticeXP2 sysDSP Usage Guide
- TN1141, LatticeXP2 sysCONFIG Usage Guide
- TN1142, LatticeXP2 Configuration Encryption and Security Usage Guide
- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology
- TN1220, LatticeXP2 Dual Boot Feature
- TN1130, LatticeXP2 Soft Error Detection (SED) Usage Guide
- TN1143, LatticeXP2 Hardware Checklist

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTL, LVCMOS, SSTL, HSTL): www.jedec.org
- PCI: <u>www.pcisig.com</u>

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